

AMENDMENTS TO THE SPECIFICATION:

Replace the Title of Invention at Page 1, lines 1-2 with the following Title of Invention:

08/11/05
GN
APPARATUS

METHOD OF SEALING WAFER BACKSIDE FOR FULL-FACE PROCESSING
ELECTROCHEMICAL PLATING

Replace the paragraph at Page 1, lines 5-7 with the following paragraph:

08/4/05
GN
This application is a continuation of U.S. Application No. 09/910,686 filed on July 20, 2001, ^{U.S. PATENT NO. 6,855,037} and is related to and claims priority from U.S. Provisional Application No. 60/275,406 filed on March 12, 2001 and entitled Wafer Carrier For Wet Processes, all incorporated herein by reference.

Replace the paragraph at Page 3, lines 4-10 with the following paragraph:

In use, the carrier head is immersed into a solution, typically an electrolyte in a deposition and certain material removal processes, or a slurry in a CMP material removal process, for example. In processes where moveable contact with a pad is desired, such as for polishing, such a pad will be included. During any such process, it is important to prevent leakage of the solution to the backside of the wafer. Such leakages to the backside of the wafer contaminate the wafer backside and the electrical contacts. Removal of contaminants from the wafer backside requires an extra process step that is time consuming and increases manufacturing costs.

Replace the paragraph beginning at Page 4, line 1, with the following paragraph:

Yet another conventional CMP head is similar to the head shown in Figure 1A, but it holds the wafer from the back side by vacuum when positioning the wafer for processing and from the circumference of the wafer by a retaining ring during processing, thereby fully exposing the front surface of the wafer. While the CMP process is done over the front surface of the wafer, the slurry from the CMP process can nevertheless migrate toward the back surface of the wafer.